



10/789,638

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: David L. Bender  
Serial No.: 10/789,638  
Confirm. No. 9160  
Filed: Feb. 27, 2004

Attorney Docket: Solx 4 US  
Art Unit: 1792  
Examiner: G. Ragesh Rao  
Date: May 6, 2008

For: SYSTEM FOR CONTINUOUS  
GROWING OF MONOCRYSTALLINE  
SILICON

**Response to Restriction Requirement**

Assistant Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Restriction Requirement mailed March 14, 2008, applicant elects the invention of Group I, claims 1-11, 14, 18, 19, 20, and 27-33 drawn to an apparatus CZ system for growing a single crystal ingot from a molten crystalline material.

In paragraph two of the Detailed Action the Examiner points out that this is a followup restriction from Applicant's response filed 12/31/07, because Group I requires a further breakdown between apparatus and process.

No claims are added after this election. A claims listing is attached hereto.

Respectfully submitted,

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